

Silicon PNP Power Transistors

2SA1062

DESCRIPTION

- With TO-3PN package
- Complement to type 2SC2486
- High collector power dissipation

APPLICATIONS

- High power audio frequency amplifier

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

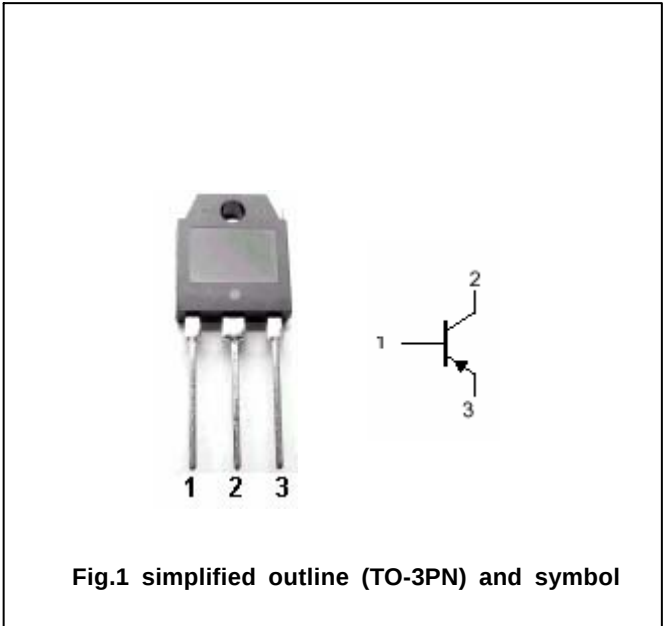


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-120	V
V _{CEO}	Collector-emitter voltage	Open base	-120	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current (DC)		-7	A
I _{CM}	Collector current-peak		-12	A
P _C	Collector power dissipation	T _C =25	80	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

Silicon PNP Power Transistors

2SA1062

CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-10mA ; I_B=0$	-120			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-5A ; I_B=-0.5A$			-2.0	V
V_{BE}	Base-emitter on voltage	$I_C=-5A ; V_{CE}=-5V$			-1.8	V
I_{CBO}	Collector cut-off current	$V_{CB}=-120V ; I_E=0$			-50	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-3V ; I_C=0$			-50	μA
h_{FE-1}	DC current gain	$I_C=-20mA ; V_{CE}=-5V$	20			
h_{FE-2}	DC current gain	$I_C=-1A ; V_{CE}=-5V$	40		200	
h_{FE-3}	DC current gain	$I_C=-5A ; V_{CE}=-5V$	20			
f_T	Transition frequency	$I_C=-0.5A ; V_{CE}=-5V$		20		MHz

◆ h_{FE-2} Classifications

R	Q	P
40-80	60-120	100-200

2SA1062

Fig.2 outline dimensions (unindicated tolerance: $\pm 0.10\text{mm}$)